

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	13	koh near kwan.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:24
2	BRS	L2	0	(oxynitride-nitride- oxynitride) near15 (polysilicon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:25
3	BRS	L3	548	(oxide-nitride-oxide) near15 (polysilicon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:27

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	2015	((oxide-nitride-oxide) or (ono)) near15 (polysilicon)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:27
5	BRS	L5	171	((oxide-nitride-oxide) or (ono)) near15 (polysilicon) near25 (tunnel)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:28
6	BRS	L6	281	((oxide-nitride-oxide) or (ono)) near15 (polysilicon) near25 (tunnel or oxide) near25 (wafer or substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/0 7 18:28

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	2	((oxide-nitride-oxide) or (ono)) near15 (polysilicon) near25 (tunnel or oxide) near25 (wafer or substrate) near25 (well near15 channel)	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/07 18:29
8	BRS	L8	8	((oxide-nitride-oxide) or (ono)) near15 (polysilicon) near25 (tunnel or oxide) near25 (wafer or substrate) near25 (sti or trench near3 isolation)	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/07 18:45
9	BRS	L9	281	((oxide-nitride-oxide) or (ono)) near15 (polysilicon) near25 (tunnel or oxide) near25 (wafer or substrate)	US-PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2004/12/07 18:45

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	283	((oxide-nitride-oxide) or (ono)) near15 (polysilicon or polysilicon) near25 (tunnel or oxide) near25 (wafer or substrate)	US-PGPUB ; USPAT ; EPO ; JPO ; DERWE NT ; IBM_T DB	2004/12/07 18:57
11	BRS	L11	286	((oxide-nitride-oxide) or (ono)) near15 (polysilicon or polysilicon or poly near silicon) near25 (tunnel or oxide) near25 (wafer or substrate)	US-PGPUB ; USPAT ; EPO ; JPO ; DERWE NT ; IBM_T DB	2004/12/07 18:57
12	BRS	L12	286	((oxide-nitride-oxide) or (ono)) near15 ((polysilicon or polysilicon) or (poly near silicon)) near25 (tunnel or oxide) near25 (wafer or substrate)	US-PGPUB ; USPAT ; EPO ; JPO ; DERWE NT ; IBM_T DB	2004/12/07 18:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	15	((oxide-nitride-oxide) or (ono)) near15 ((polysilicon or polysilicon) or (poly near silicon)) near25 (tunnel or oxide) near25 (wafer or substrate) near25 (channel)	US-PGPUB; USPAT; EPO; JPO; DERWE NT; IBM_T DB	2004/12/07 18:57

	U	1	Document ID	Title	Current OR
1			US 6828197 B1	Method for fabricating nitride read only memory	438/275
2			US 6436778 B1	Re-oxidation approach to improve peripheral gate oxide integrity in a tunnel nitride oxidation process	438/305
3			US 6376877 B1	Double self-aligning shallow trench isolation semiconductor and manufacturing method therefor	257/317
4			TW 474011 A	Manufacture of trench-type flash memory increases capacitor coupling ratio to improve device performance	
5			US 6121148 A	Formation of a polysilicon-contacted trench isolation structure by etching an exposed portion of the substrate's surface, etching the trench lining silicon nitride, and depositing another polysilicon layer	

	U	1	Document ID	Title	Current OR
6			TW 388131 A	Improving the coupling ratio of wordline of stacked gate flash memory element to floating gate comprises sequentially forming a first oxide layer, a first nitride layer on a semiconductor wafer; defining a trench isolat	
7			US 5851881 A	Multi-level logic flash memory cell, EEPROM - comprises a poly stacked gate transistor in series with a MONOS transistor	
8			US 5506160 A	Alternate metal ground EPROM device fabrication with scaling to 0.6 micron - allowing formation of 64 mega bit EPROM arrays	